

METHOD TO PLANARIZE AND REDUCE DEFECT DENSITY OF SILICON GERMANIUM

Abstract of the Disclosure

A method for blanket depositing a SiGe film comprises intermixing a silicon source, a germanium source and an etchant to form a gaseous precursor mixture. The method further comprises flowing the gaseous precursor mixture over a substrate under chemical vapor deposition conditions to deposit a blanket layer of epitaxial SiGe onto the substrate, whether patterned or un-patterned.

PATENT

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